JJMICROELECTRONICS

100V, 210A, 2.0mΩ N-channel Power SGT MOSFET

JMSH1002PE

Features
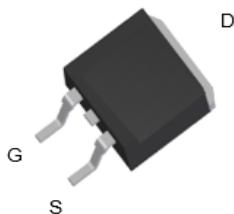
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS TESTED
- 100% ΔVds TESTED
- Halogen-free; RoHS-compliant
- Pb-free plating

Applications

- Load Switch
- PWM Application
- Power Management

Product Summary

Parameters	Value	Unit
V_{DSS}	100	V
$V_{GS(th)\_Typ}$	3.0	V
$I_D(@V_{GS}=10V)$	210	A
$R_{DS(ON)\_Typ}(@V_{GS}=10V$	2.0	mΩ

RoHS

Lead-free Green

TO-263-3L Top View

Pin Assignment

Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH1002PE	SH1002P	3	Tape&Reel	TO-263-3L	800	4000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		100	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	$T_C = 25°C$	210	A
		$T_C = 100°C$	149	
I_{DM}	Pulsed Drain Current [1]		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy [2]		1272	mJ
P_D	Power Dissipation	$T_C = 25°C$	274	W
		$T_C = 100°C$	110	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient [3]	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.5	

Electrical Characteristics (T_J = 25°C unless otherwise specified)
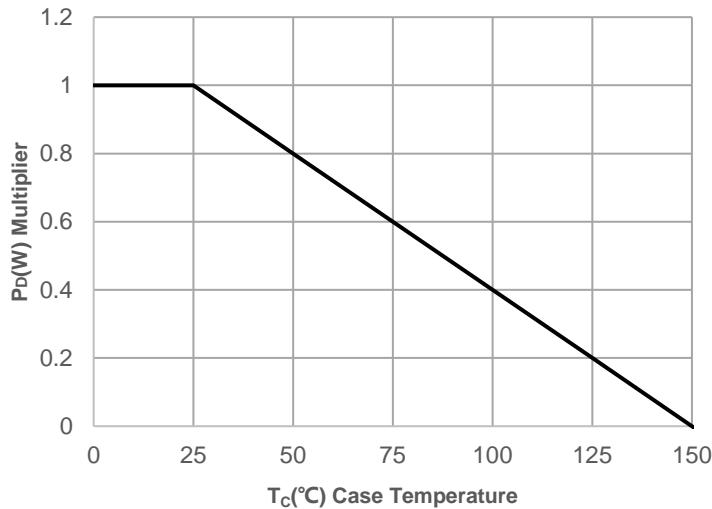
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.1	3.0	3.9	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance[4]	V_{GS} = 10V, I_D = 20A	-	2.0	2.8	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	0.7	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz	-	8773	-	pF
C_{oss}	Output Capacitance		-	1551	-	pF
C_{rss}	Reverse Transfer Capacitance		-	31	-	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V, V_{DS} = 50, I_D = 20A	-	130	-	nC
Q_{gs}	Gate Source Charge		-	41	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	30	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 50V, I_D= 20A, R_{GEN} = 3Ω	-	28	-	ns
t_r	Turn-On Rise Time		-	26	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	57	-	ns
t_f	Turn-Off Fall Time		-	24	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	210	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	841	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 15A, di/dt = 100A/us	-	84	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	175	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=50V, V_G=10V, R_G=25ohm, L=3mH, I_{AS}=29.12A, V_{DD}=0V during time in avalanche.

3. $R_{θJA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.

4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.
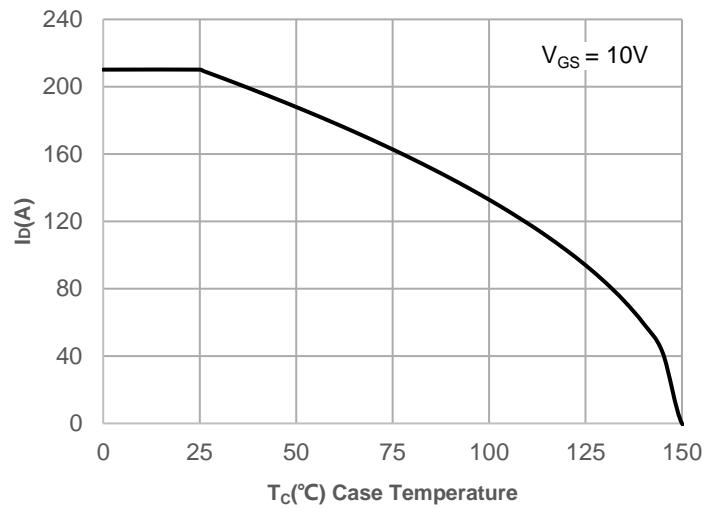
# Typical Performance Characteristics

Figure 1: Power De-rating

P_D(W) Multiplier vs T_C(℃) Case Temperature
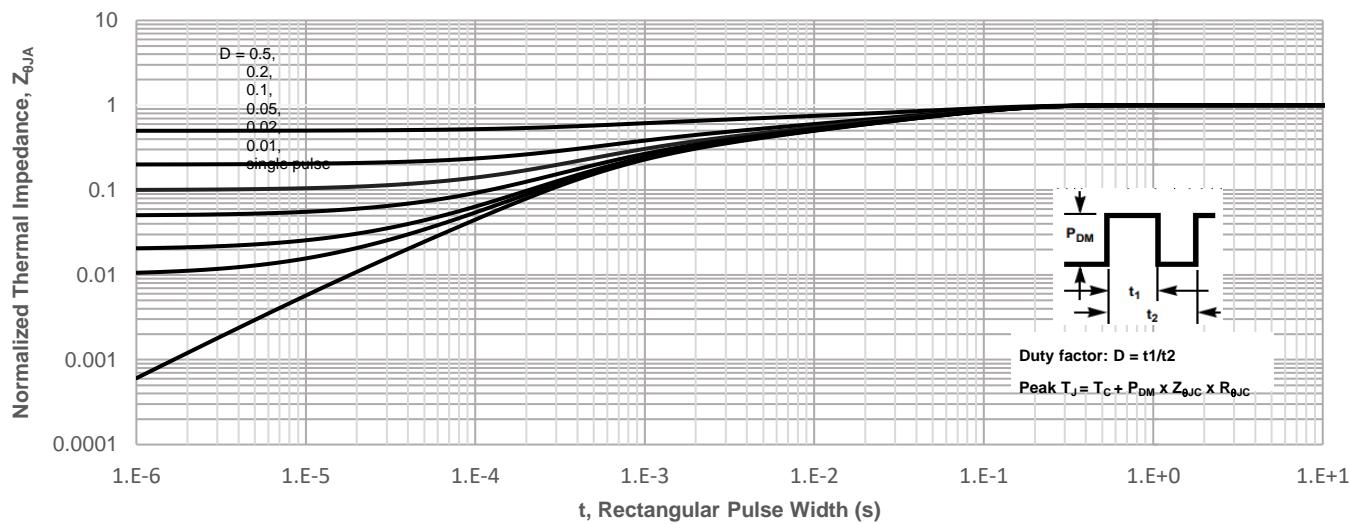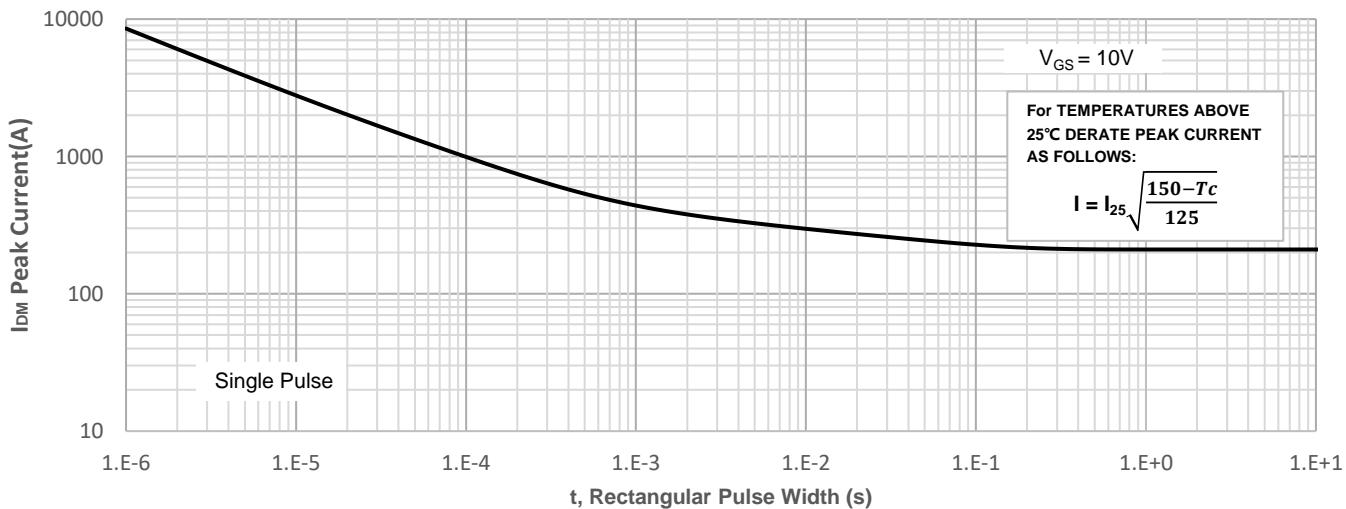
Figure 2: Current De-rating

I_D(A) vs T_C(℃) Case Temperature

V_{GS} = 10V

Figure 3: Normalized Maximum Transient Thermal Impedance

Normalized Thermal Impedance, $Z_{\theta JA}$

D = 0.5,
0.2,
0.1,
0.05,
0.02,
0.01,
single pulse

P_{DM}

t_1
t_2

Duty factor: D = t1/t2

Peak T_J = T_C + P_{DM} x $Z_{\theta JC}$ x $R_{\theta JC}$

t, Rectangular Pulse Width (s)
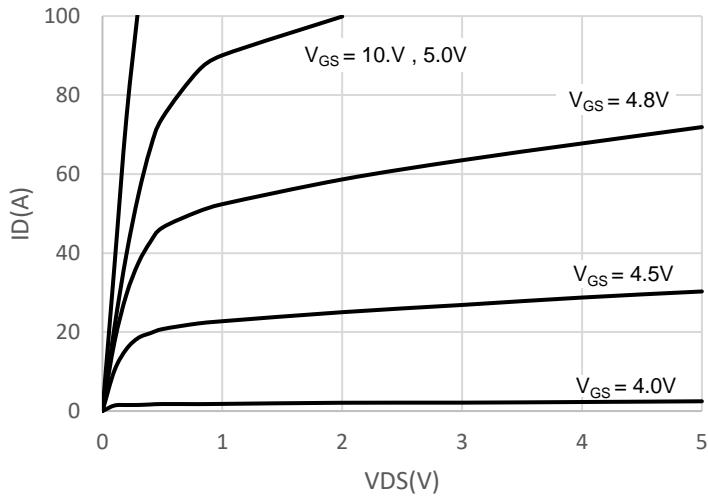
Figure 4: Peak Current Capacity

I_{DM} Peak Current(A) vs t, Rectangular Pulse Width (s)

V_{GS} = 10V

For TEMPERATURES ABOVE 25℃ DERATE PEAK CURRENT AS FOLLOWS:

$$I = I_{25}\sqrt{\frac{150-Tc}{125}}$$

Single Pulse

REV 1.0 | 3/7
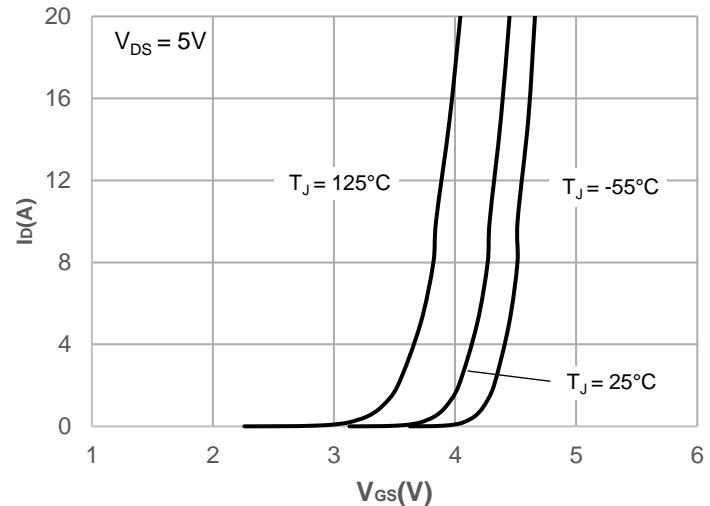
Typical Performance Characteristics
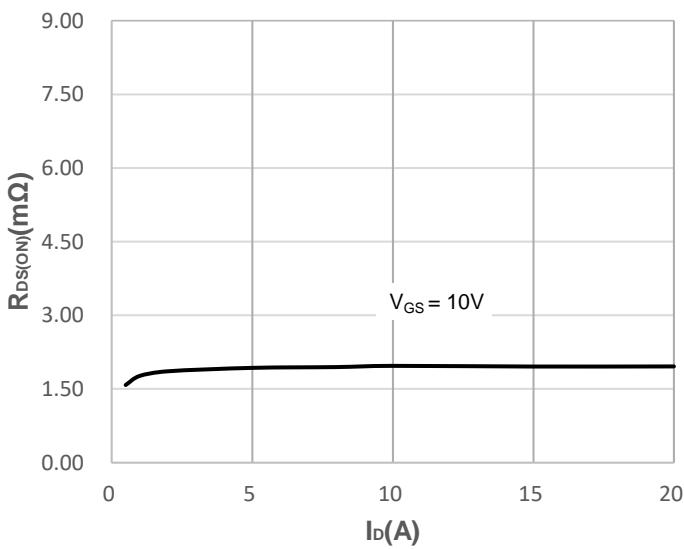
Figure 5: Output Characteristics
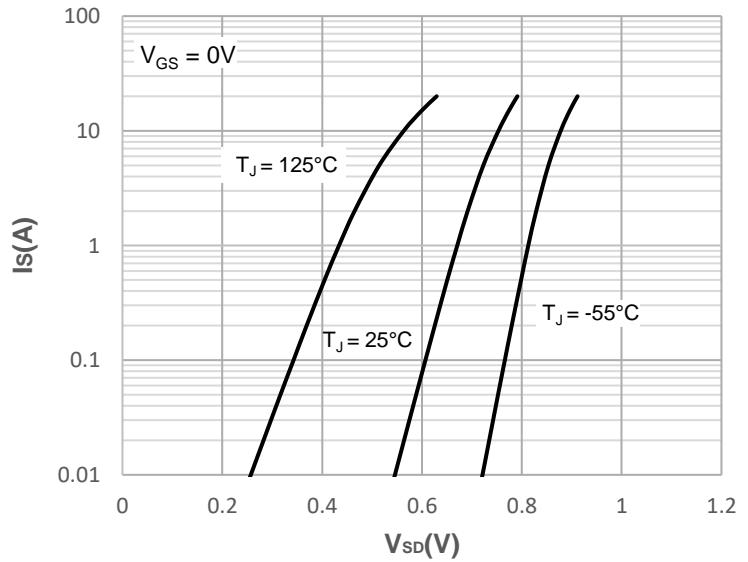
**Figure 6: Typical Transfer Characteristics**
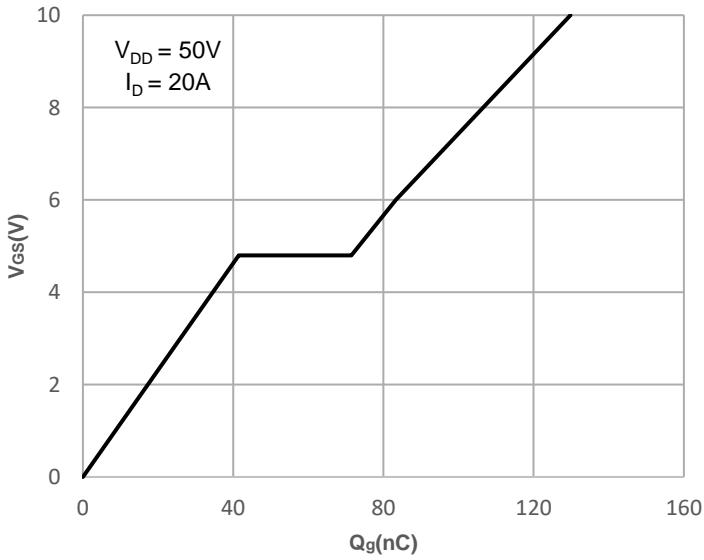
**Figure 7: On-resistance vs. Drain Current**
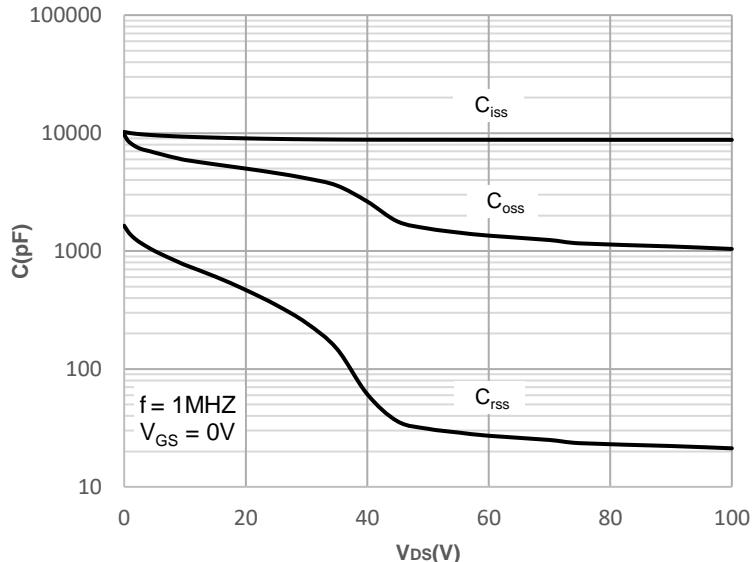
**Figure 8: Body Diode Characteristics**


Figure 9: Gate Charge Characteristics
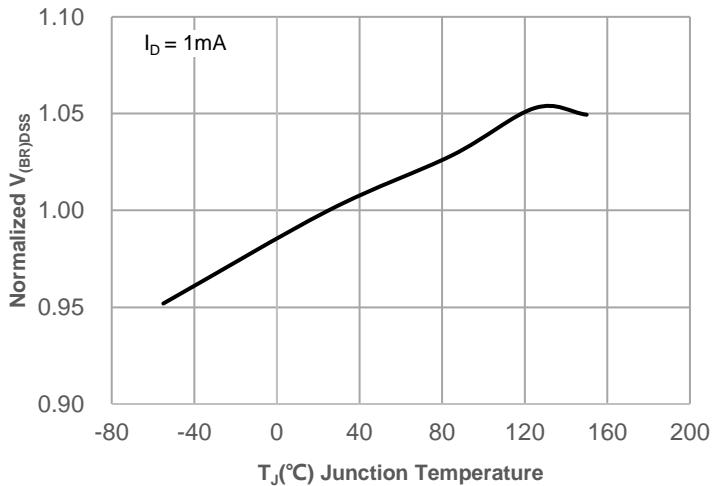
Figure 10: Capacitance Characteristics
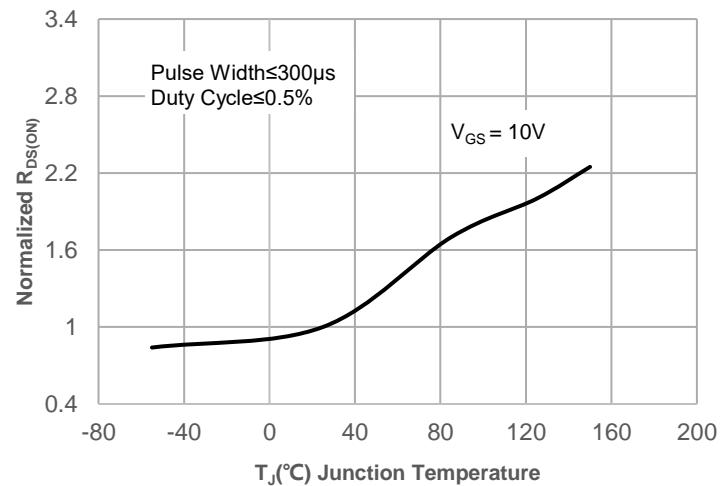
Typical Performance Characteristics
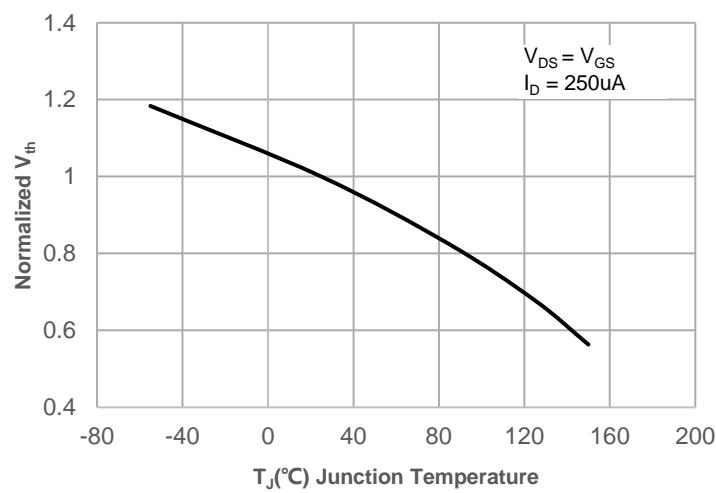
Figure 11: Normalized Breakdown voltage vs. Junction Temperature

$I_D = 1mA$

Normalized $V_{(BR)DSS}$ vs. T_J(℃) Junction Temperature
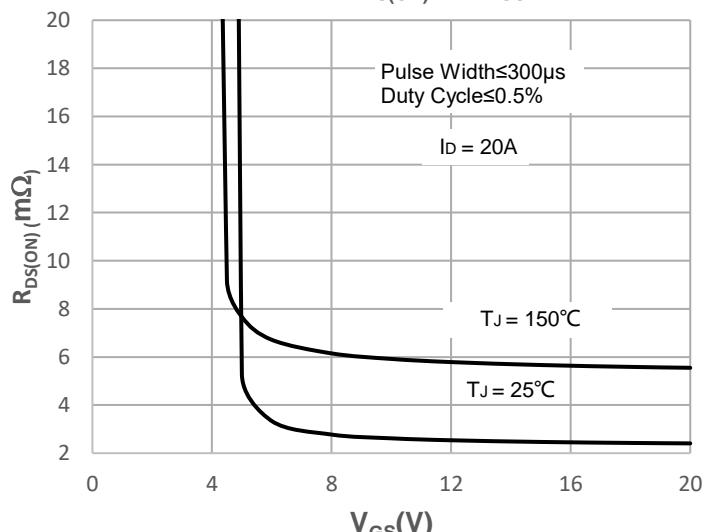
Figure 12: Normalized on Resistance vs. Junction Temperature

Pulse Width≤300μs
Duty Cycle≤0.5%

$V_{GS} = 10V$

Normalized $R_{DS(ON)}$ vs. T_J(℃) Junction Temperature
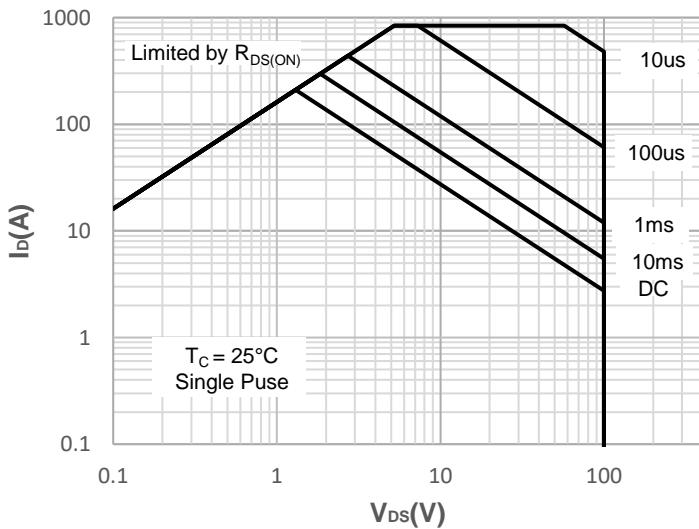
Figure 13: Normalized Threshold Voltage vs. Junction Temperature

$V_{DS} = V_{GS}$
$I_D = 250uA$

Normalized V_{th} vs. T_J(℃) Junction Temperature

Figure 14: $R_{DS(ON)}$ vs. V_{GS}

Pulse Width≤300μs
Duty Cycle≤0.5%

$I_D = 20A$

$T_J = 150℃$

$T_J = 25℃$

$R_{DS(ON)}$ (mΩ) vs. V_{GS}(V)
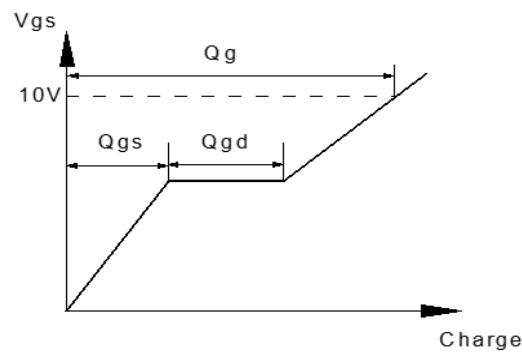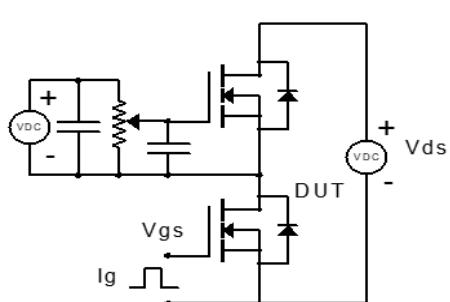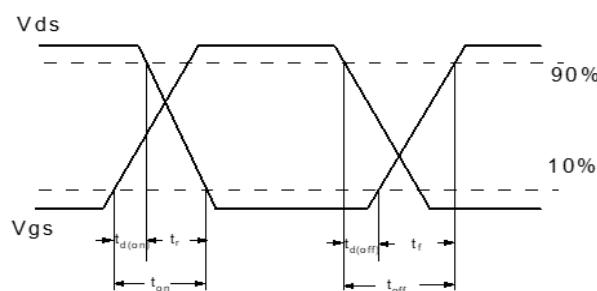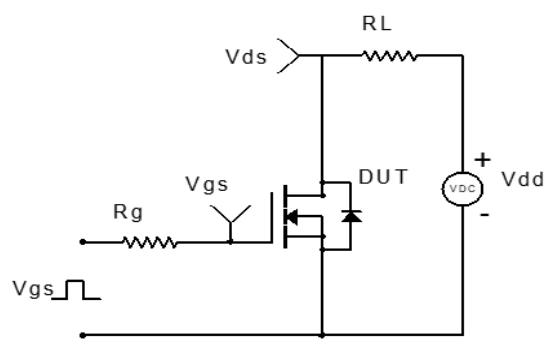
Figure 15: Maximum Safe Operating Area

Limited by $R_{DS(ON)}$

10us
100us
1ms
10ms
DC

$T_C = 25℃$
Single Puse

I_D(A) vs. V_{DS}(V)
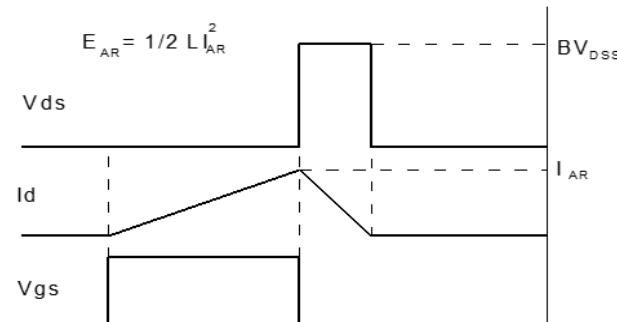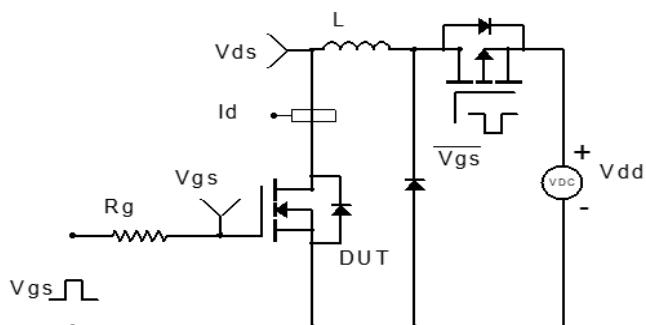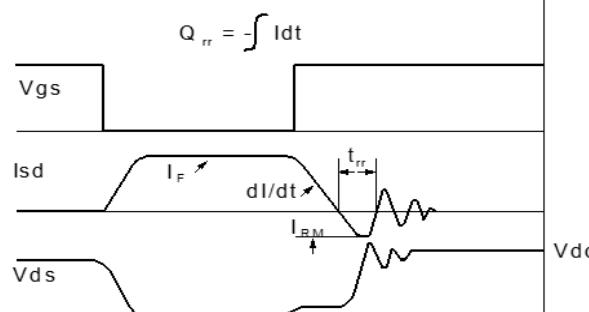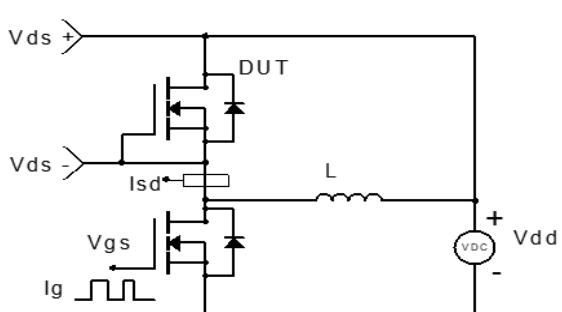
# Test Circuit

Figure 1: Gate Charge Test Circuit & Waveform

Figure 2: Resistive Switching Test Circuit & Waveform
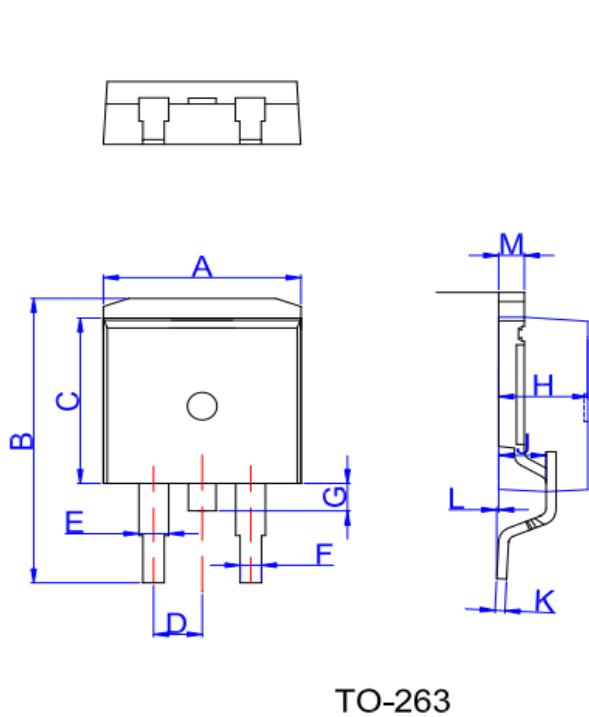
Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

$E_{AR} = 1/2\ L I_{AR}^2$

$Q_{rr} = \int I dt$

Figure 4: Diode Recovery Test Circuit & Waveform

REV 1.0 | 6/7

Package Mechanical Data(TO-263-3L)

TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

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